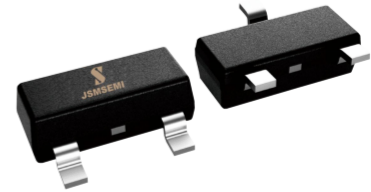
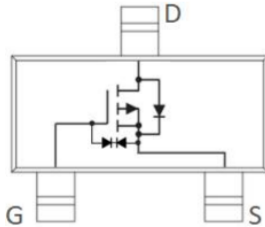


◆ Features & Applications

Super high density cell design for extremely low RDS(ON) .
 Exceptional on-resistance and maximum DC current capability.
 ESD Protection.


◆ Absolute Maximum Ratings(Ta=25°C)

Symbol	Parameter	Value	Unit
V _{DS}	Drain-Source Voltage	-50	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Continuous Drain Current	-0.13	A
I _{DM}	Pulsed Drain Current (tp=10s)	-0.5	A
P _D	Power Dissipation	350	mW
R _{θJA}	Thermal Resistance From Junction To Ambient (t≤5s)	350	°C/W
T _J , T _{stg}	Operation Junction And Storage Temperature Range	-55~+150	°C

◆ Electrical Characteristics (Ta=25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
Static						
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} =0, I _D =250μA	-50			V
V _{GS(th)}	Gate threshold voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.8		-2.0	V
I _{GSS}	Gate-body leakage current	V _{DS} =0, V _{GS} =±10V			±10	μA
I _{DSS}	Zero gate voltage drain current	V _{DS} =-50V, V _{GS} =0V			-10	μA
		V _{DS} =-40V, V _{GS} =0V			-100	nA
R _{DS(on)}	Drain-source on-resistance ^a	V _{GS} =-10V, I _D =-0.13A		2	5	Ω
		V _{GS} =-4.5V, I _D =-0.13A		2.5	6	Ω
g _{FS}	Forward transconductance ^a	V _{DS} =-25V, I _D =-0.13A	50			mS
V _{SD}	Diode forward voltage	I _S =-0.13A, V _{GS} =0V			-1.0	V
Dynamic						
C _{iss}	Input capacitance	V _{DS} =-25V, V _{GS} =0V, f=1MHz		25		pF
C _{oss}	Output capacitance			15		
C _{rss}	Reverse transfer capacitance ^b			3.5		
Switching^b						
t _{d(on)}	Turn-on delay time	V _{GS} =-10V, V _{DS} =-15V I _D =-200mA, R _{GEN} =25Ω		16.7		nS
t _r	Rise time			8.6		
t _{d(off)}	Turn-off delay time			17.9		
t _f	Fall time			5.3		

Notes :

a. Pulse Test : Pulse width≤300μs, duty cycle ≤2%.

b. Guaranteed by design, not subject to producing.

◆ Typical Characteristics

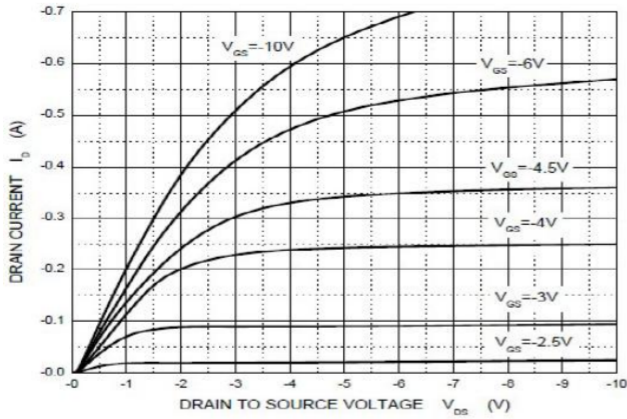


Figure1. Output Characteristics

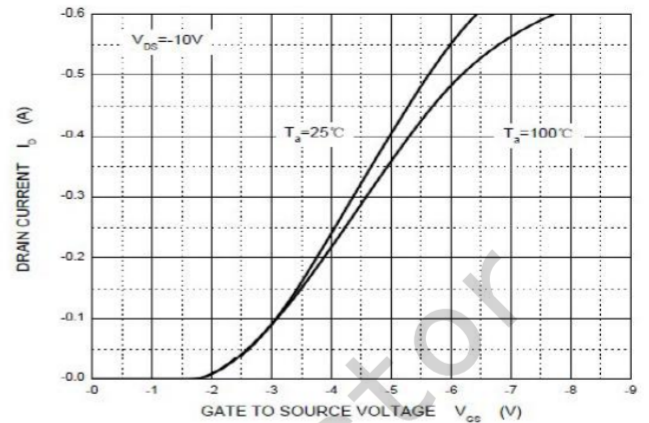


Figure2. Transfer Characteristics

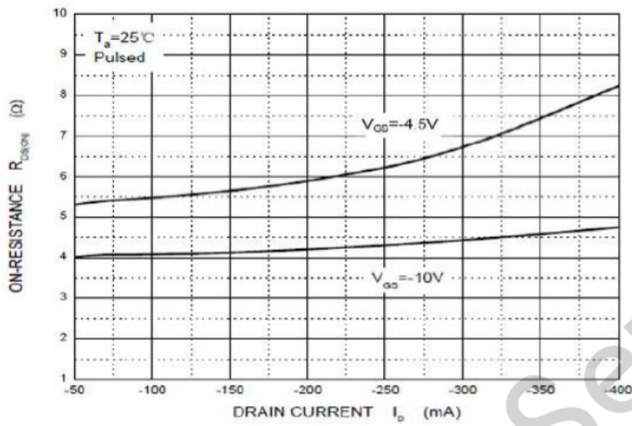


Figure3. Drain-Source on Resistance

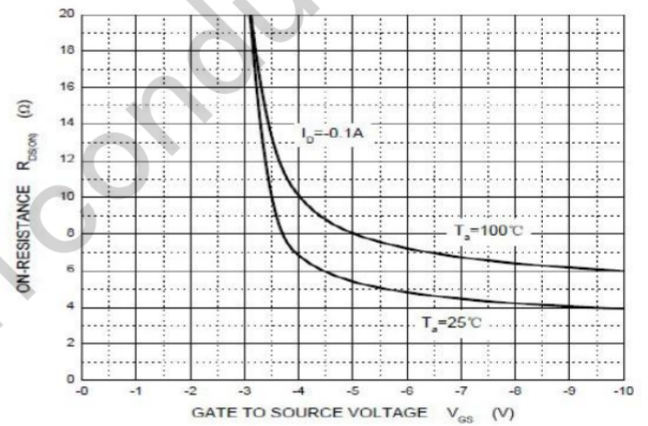


Figure4. Drain-Source on Resistance

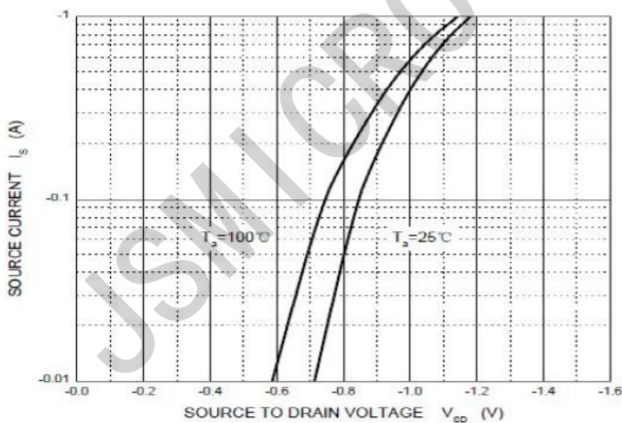


Figure5. Diode Forward Voltage vs. current

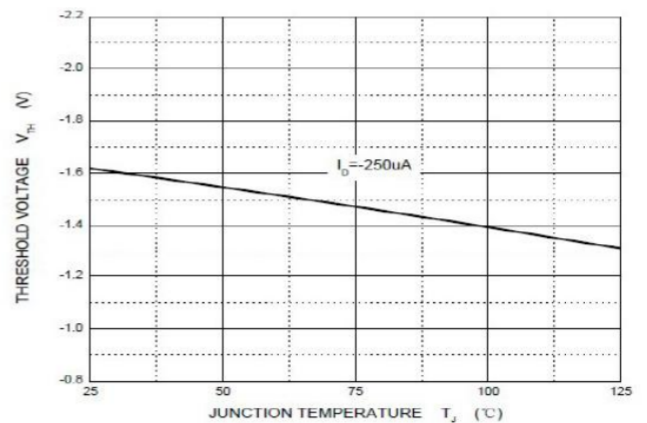
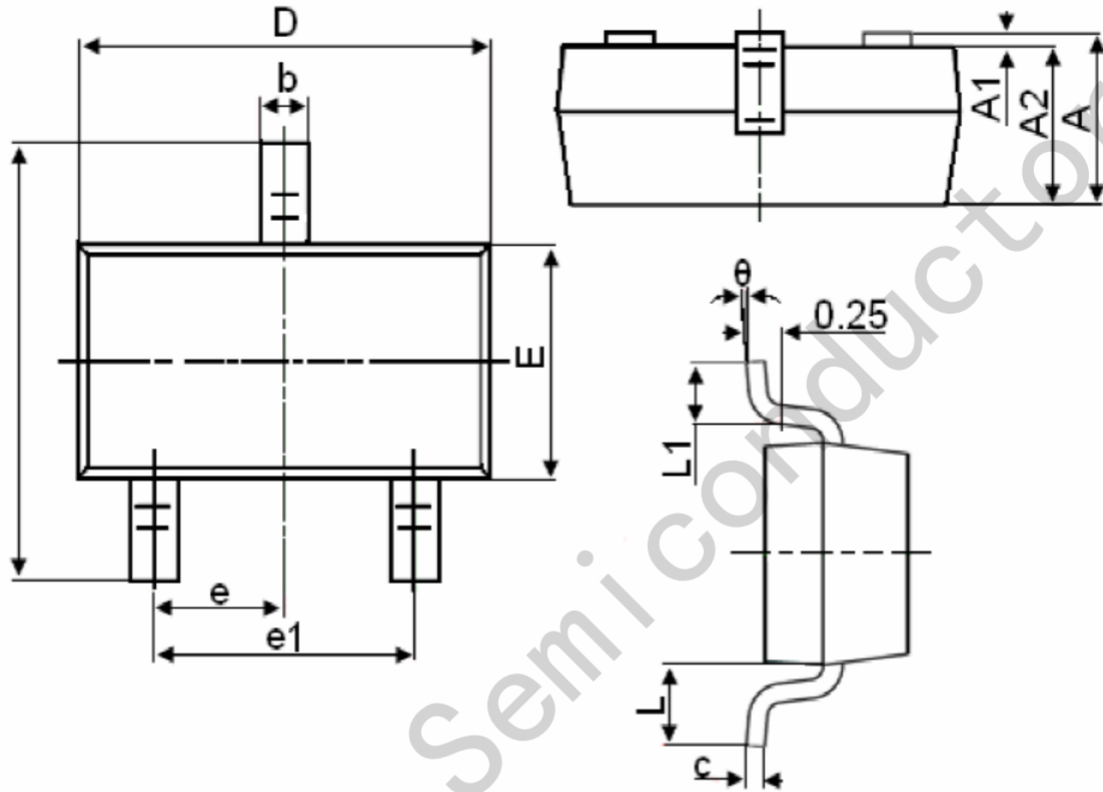


Figure6. Gate Threshold vs. Junction Temperature

Package Information

SOT-23



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

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